

SOT-227 Silicon Carbide Single Phase Bridge, 50 A



SOT-227

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _O at T _C = 136 °C	50 A					
V_{RRM}	1200 V					
V_{FM} at 50 A, T_C = 25 °C	1.5 V					
Туре	Modules - diode, SiC Schottky					
Package	SOT-227					
Circuit configuration	Single phase bridge					

FEATURES

Virtually no recovery tail and no switching losses



 Majority carrier diode using Schottky technology on SiC wide band gap material ROHS

- Improved V_F and efficiency by thin wafer technology
- · High speed switching, low switching losses
- Positive temperature coefficient, for easy paralleling
- Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
1	180° rect. conduction angle	50	Α		
IO	T _C	136	°C		
I _{FSM}	50 Hz	328	۸		
	60 Hz	343	Α		
l ² t	50 Hz	538	A ² s		
1-1	60 Hz	491	A-5		
V _{RRM}		1200	V		
T _J		-40 to +175	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS		
TYPE NUMBER	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V
VS-SC50BA120	1200	1200



ELECTRICAL SPECIFICATIONS PER DIODE (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 200 μA	1200	-	-	
Forward voltage	V	I _F = 50 A		1.5	1.73	V
Forward voltage	orward voltage V _{FM}	I _F = 50 A, T _J = 150 °C	-	2.13	-	
		V _R = 1200 V	-	1.3	120	
Reverse leakage current	I _{RM}	T _J = 125 °C, V _R = 1200 V	-	4.4	-	μΑ
	T _J = 150 °C, V _R = 1200 V	-	6.6	-		
Junction capacitance	C _T	V _R = 1200 V, f = 1 MHz	-	136	-	pF

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum DC output current	1-	Resistive or inductive load		50	Α	
at case temperature	I _O				136	°C
	t = 10 ms No voltage		No voltage		328	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		343	А
non-repetitive forward current	IFSM	t = 10 ms	100 % V _{RBM}	Ja: 11 05 00	276	
		t = 8.3 ms	reapplied		288	
Na	l ² t	t = 10 ms	No voltage	Initial T _J = 25 °C	538	A ² s
		t = 8.3 ms	reapplied		491	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}		380	
		t = 8.3 ms reapplied	reapplied		347	
Maximum l²√t for fusing	I²√t	I^2t for time $t_x = I_2 \sqrt{t} \times \sqrt{t_x}$; $0.1 \le t_x \le 10$ ms, $V_{RRM} = 0$ V			5.38	kA²√s
Low level of threshold voltage, per leg	V _{F(T0)1}	$(16.7 \% \times \pi \times I_{E(AV)}) < I < \pi \times I_{E(AV)}, T_{.I} = T_{.I} \text{ maximum}$			0.88	V
Low level value of forward slope resistance	r _{f1}				mΩ	
High level of threshold voltage, per leg	V _{F(T0)2}	(I > π x I _{F(AV)}), T _J = T _J maximum 1.01 31.16			1.01	V
High level value of forward slope resistance	r _{f2}				mΩ	

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total capacitive charge	Q _C	V _R = 800 V	-	223	1	nC

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction-to-case, per diode	R _{thJC}		-	-	0.62	°C/W
Case-to-heatsink	R _{thCS}	Flat, greased surface	-	0.1	-	C/VV
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SC	T-227	



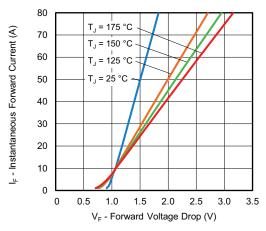


Fig. 1 - Typical Forward Voltage Drop Characteristics

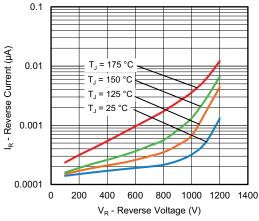


Fig. 2 - Typical Values of Reverse Current vs Reverse Voltage

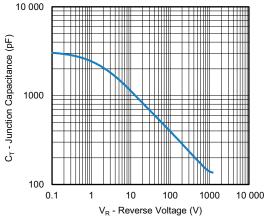


Fig. 3 - Junction Capacitance vs. Reverse Voltage

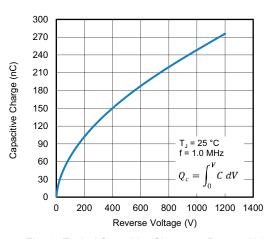


Fig. 4 - Typical Capacitive Charge vs. Reverse Voltage

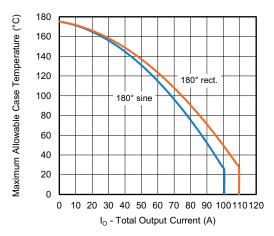


Fig. 5 - Current Rating Characteristics

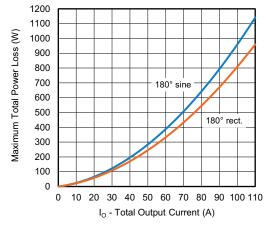


Fig. 6 - Total Power Loss Characteristics



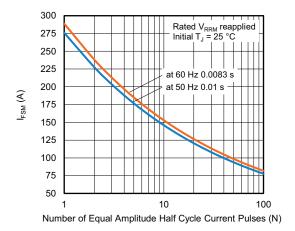


Fig. 7 - Non-Repetitive Peak Forward Surge Current vs. Number Pulses

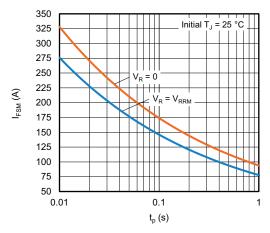


Fig. 8 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration

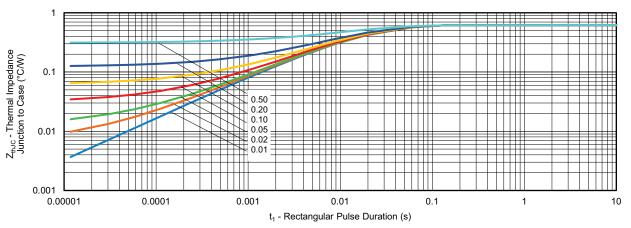
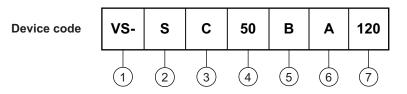


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



1 - Vishay Semiconductors product

2 - Silicon Carbide diode

Present silicon generation

4 - Current rating (50 = 50 A)

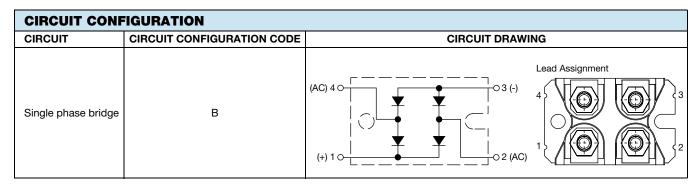
5 - Circuit configuration (single phase bridge)

6 - Package indicator (SOT-227 standard insulated base)

7 - Voltage rating (120 = 1200 V)

Quantity per tube is 10, M4 screw and washer included





LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Part marking information	www.vishay.com/doc?95425



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